

# 제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

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## G. Device & Process Modeling, Simulation and Reliability 분과

Room C  
1F / 106호

2015년 2월 12일(목) 13:10-14:40

### [TC2-G] Device Physics and Characterization 2

좌장: 이성현 (한국외국어대학교), 박문수 (삼성디스플레이)

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| TC2-G-1 | 13:10-13:25 | <b>Extraction of Distance between Interface Trap and Oxide Trap from Random Telegraph Noise in Gate-Induced Drain Leakage</b><br>Youngsoo Seo, Sung-Won Yoo, Joonha Shin, Hyunsoo Kim, Hyunsuk Kim, Sangbin Jeon, and Hyungcheol Shin<br>Inter-university Semiconductor Research Center (ISRC) and School of Electrical Engineering and Computer Science, Seoul National University |
| TC2-G-2 | 13:25-13:40 | <b>The Influence of Dummy Pattern on the RF Inductor Characteristics in 90nm CMOS Chip Layout</b><br>Jong Keun Kim, Hee Kyeong Yang, Myoung Jun Jang, In Wook Cho, and Kyung Dong Yoo<br>Technology Development in Image Development Group, Sk Hynix Inc.   |
| TC2-G-3 | 13:40-13:55 | <b>Cost-Effective Approach using Deep N-type Well Junction in 180nm BCDMOS Technology</b><br>Sekyung Oh, Daehoon Kim, Kwangsik Ko, Jaeho Hwang, Soonyeol Park, Jina Eum, Joowon Park, Kuemju Lee, Sanghyun Lee, Inwook Cho, and Kyungdong Yoo<br>Technology Development team, SK Hynix Inc.   |
| TC2-G-4 | 13:55-14:10 | <b>Origin of Kink Phenomenon in <math>S_{11}</math>-Parameter of Standard RF MOSFETs</b><br>Ja-Hyun Ahn and Seonghearn Lee<br>Department of Electronic Engineering, Hankuk University of Foreign Studies  |
| TC2-G-5 | 14:10-14:25 | <b>A Characteristic Method of Extracting Intrinsic Threshold Voltage Fluctuation from Depletion Charge Variation</b><br>Dongseok Cho, Jaekyu Lee, Junhee Lim, Jaerok Kahng, and Satoru Yamada<br>Semiconductor R&D Center, Samsung Electronics  |
| TC2-G-6 | 14:25-14:40 | <b>Design of Robust High-Voltage MOSFETs for Source Driver Applications</b><br>Yon-Sup Pang, Eunkyung Park, Kwangho Park, Gukhwan Kim, Leeyeun Hwang, Boseok Oh, Sung-Bum Park, Jung Lee, and Taejong Lee<br>MagnaChip Semiconductor, Corporate Engineering   |